21 W × 4-Channel BTL Power IC

HITACHI

ADE-207-107 1st. Edition

Description

HA13150A is a four-channel BTL amplifier IC designed for car audio, featuring high output and low distortion, and applicable to digital audio equipment. It provides 21 W output per channel, with a 14.4 V power supply and at 10% distortion.

Functions

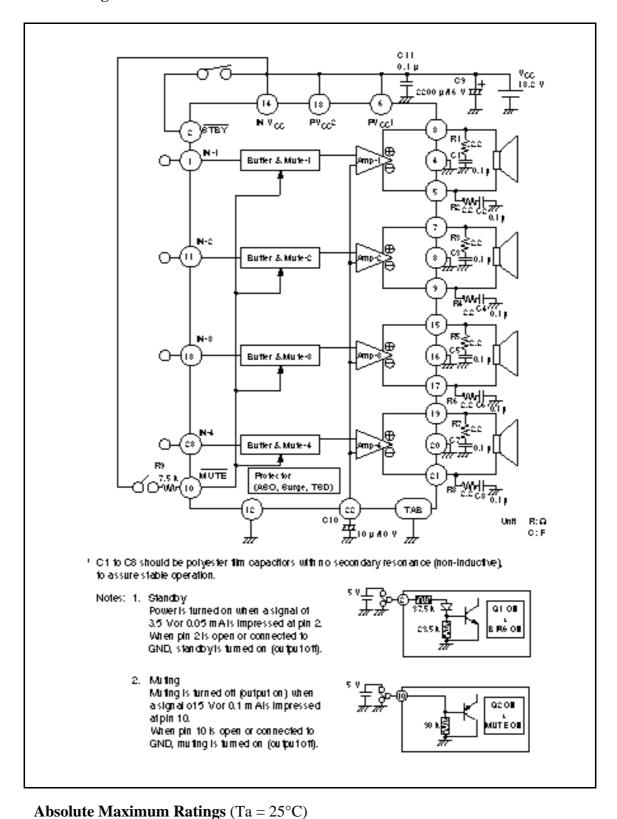
- · Built-in standby circuit
- Built-in muting circuit
- Built-in protection circuits (surge, TSD, and ASO)

Features

- Requires few external parts
- Low distortion (total harmonic distortion = 0.01% at 3 W)
- Low noise (at Rg = 620 , noise is 0.15 mV (muting off) or 0.1 mV (muting on))
- Popping noise minimized
- Highly reliable current-limiting ASO protector keeps speakers safe from all kinds of trouble.
 Reliability is further enhanced by a fast-acting thermal shutdown protection circuit with on/off hysteresis.



Block Diagram



Symbol

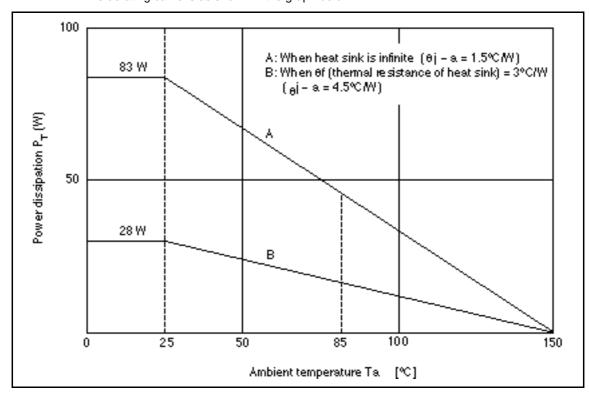
Rating

Item

				HA13150A
Operating supply voltage	V _{cc}	18	V	
Supply voltage when no signal *1	V _{cc} (DC)	26	V	
Peak supply voltage *2	V _{cc} (PEAK)	50	V	
Output current *3	I _o (PEAK)	4	Α	
Power dissipation *4	P _T	83	W	
Junction temperature	Tj	150	°C	
Operating temperature	Topr	-30 to +85	°C	
Storage temperature	Tstg	-55 to +125	°C	

Notes: 1. Tolerance within 30 seconds

- 2. Tolerance in surge pulse waveform
- 3. Value per 1 channel
- 4. Value when attached on the infinite heat sink plate at Ta = 25°C. The derating carve is as shown in the graph below.



Electrical Characteristics (V $_{CC}$ = 13.2 V, f = 1 kHz, R_L = 4 $\,$, Rg = 620 $\,$, Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Current when no signal	lq1	_	240	_	mA	Vin = 0
Output offset voltage	Vq	-250	0	+250	mV	
Gain	Gv	30.5	32	33.5	dB	
Gain difference between channels	Gv	-1.5	0	+1.5	dB	
Rated output power	Po	_	18	_	W	$V_{cc} = 13.2 \text{ V}$ $R_L = 4$, THD = 10%
Max output power	Pomax	_	30	_		$V_{cc} = 13.7 \text{ V}$ $R_L = 4$, THD = Max
Total harmonic distortion	T.H.D	_	0.01	_	%	Po = 3 W
Output noise voltage	WBN	_	0.15	0.5	mVrms	Rg = 0 BW = 20 to 20 kHz
Ripple rejection	SVR	_	55	_	dB	Rg = 600 f = 120 Hz
Channel crosstalk	C.T	_	70	_	dB	Rg = 600 Vout = 0 dBm
Input impedance	Rin	_	25	_	k	
Standby current	lq2	_	_	200	μΑ	
Standby control voltage (high)	$V_{\mathtt{STH}}$	3.5	_	V_{cc}	V	
Standby control voltage (low)	V _{STL}	0	_	1.5	V	
Muting control voltage (high)	V_{MH}	3.5	_	V _{cc}	V	
Muting control voltage (low)	V_{ML}	0	_	1.5	V	
Muting attenuation	A_{TTM}	_	70	_	dB	Vout = 0 dBm

Pin Explanation

Pin No.	Symbol	Functions	Input Impedance	DC Voltage	Equivalence Circuit
1	IN1	CH1 INPUT	25 k (Typ)	0 V	1 m m m m m m m m m m m m m m m m m m m
11	IN2	CH2 INPUT			
13	IN3	CH3 INPUT			
23	IN4	CH4 INPUT			
2	STBY	Standby control	90 k (at Trs. cutoff)	_	37.5 k 2 W 23.5 k
3	OUT1 (+)	CH1 OUTPUT		V _{cc} /2	3
5	OUT1 (–)				
7	OUT2 (+)	CH2 OUTPUT			
9	OUT2 (–)				
15	OUT3 (+)	CH3 OUTPUT			
17	OUT3 (–)				
19	OUT4 (+)	CH4 OUTPUT			
21	OUT4 (–)				
10	MUTE	Muting control	25 k (Typ)	_	10 \$25 k

Pin Explanation (cont)

Pin No.	Symbol	Functions	Input Impedance	DC Voltage	Equivalence Circuit
22	RIPPLE	Bias stability	_	V _{cc} /2	—————————————————————————————————————
6	PV _{cc} 1	Power of output stage	_	V _{cc}	_
18	PV _{cc} 2	-			
14	INV _{cc}	Power of input stage	_	V _{cc}	_
4	CH1 GND	CH1 power GND	_	_	_
8	CH2 GND	CH2 power GND	_		
16	CH3 GND	CH3 power GND	_		
20	CH4 GND	CH4 power GND	-		
12	IN GND	Input signal GND	_	_	_

Point of Application Board Design

- 1. Notes on Application board's pattern design
- For increasing stability, the connected line of V_{CC} and OUTGND is better to be made wider and lower impedance.
- For increasing stability, it is better to place the capacitor between V_{CC} and GND (0.1 μF) close to IC.
- For increasing stability, it is better to place C1 to C8 and R1 to R8, which are for stopping oscillation, close to IC.
- It is better to place the grounding of resistor (Rg), between input line and ground, close to INGND (Pin 12) because if OUTGND is connected to the line between Rg and INGND, THD will become worse due to current from OUTGND.

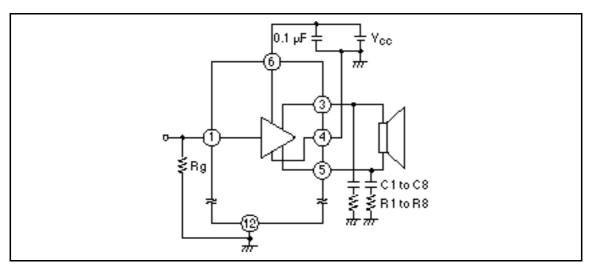


Figure 1 Notes on Application Board's Pattern Design

2. How to reduce the popping noise by Muting circuit

At normal operating circuit, Muting circuit operates at high speed under 1 μs .

In case popping noise becomes a problem, it is possible to reduce the popping noise by connecting capacitor, which determines the switching time constant, between pin 10 and GND. (Following figure 2)

We recommend value of capacitor greater then 1 μF .

Also transitional popping noise can be reduced sharply by muting before V_{CC} and Standby are ON/OFF.

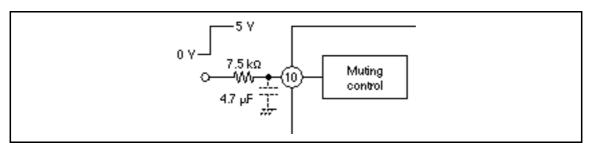
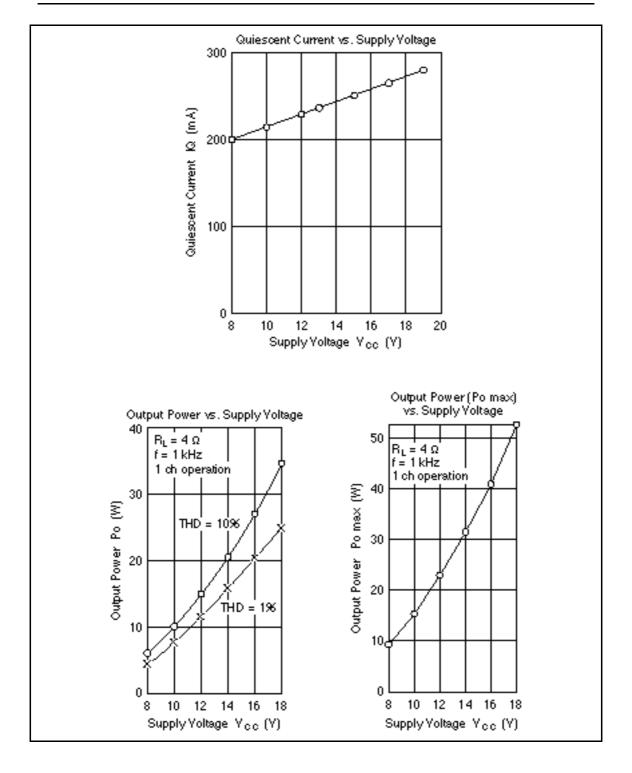
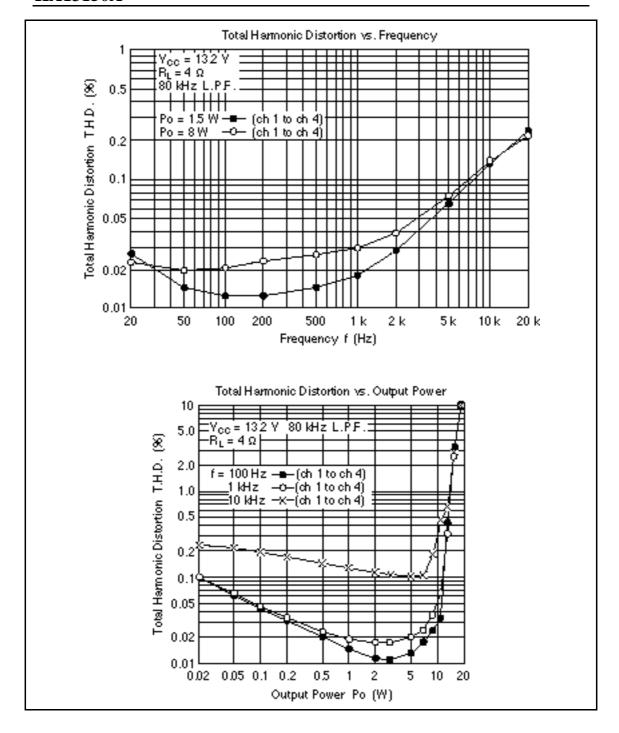


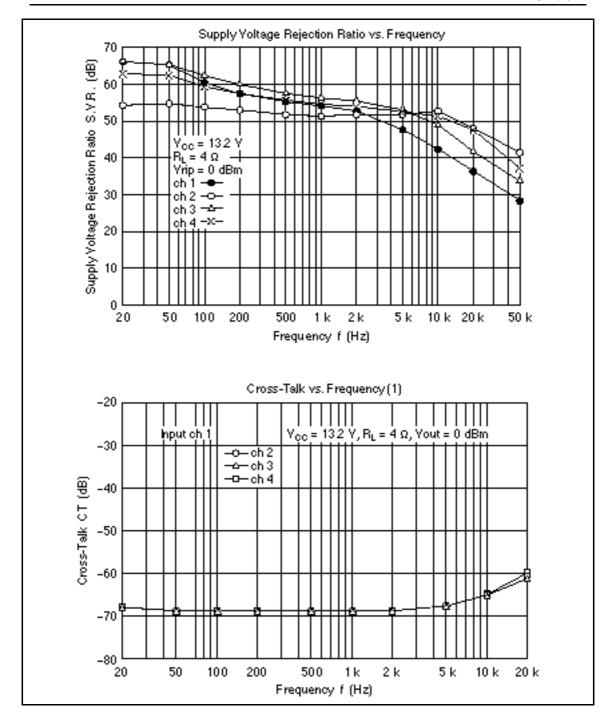
Figure 2 How to use Muting Circuit

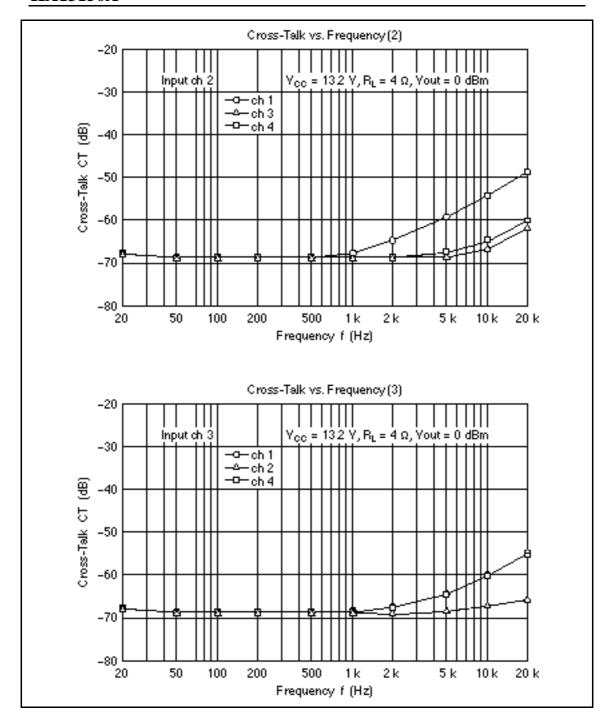
Table 1 Muting ON/OFF Time

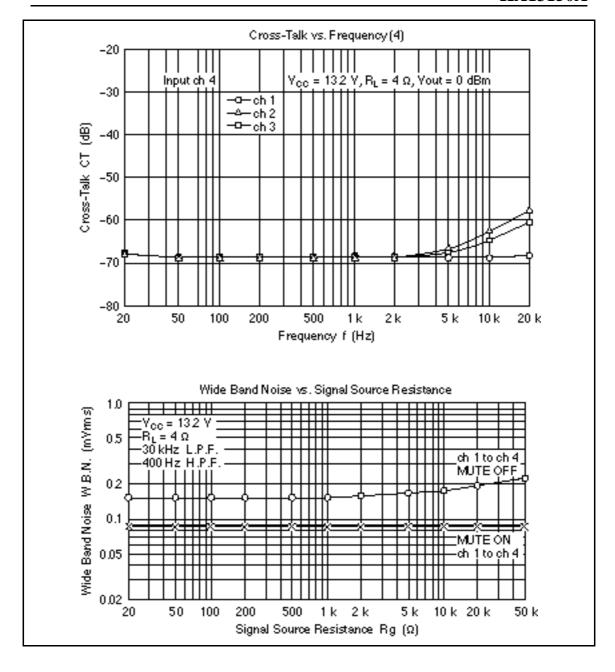
C (µF)	ON Time	OFF Time
nothing	under 1 µs	under 1 µs
0.47	2 ms	2 ms
4.7	19 ms	19 ms

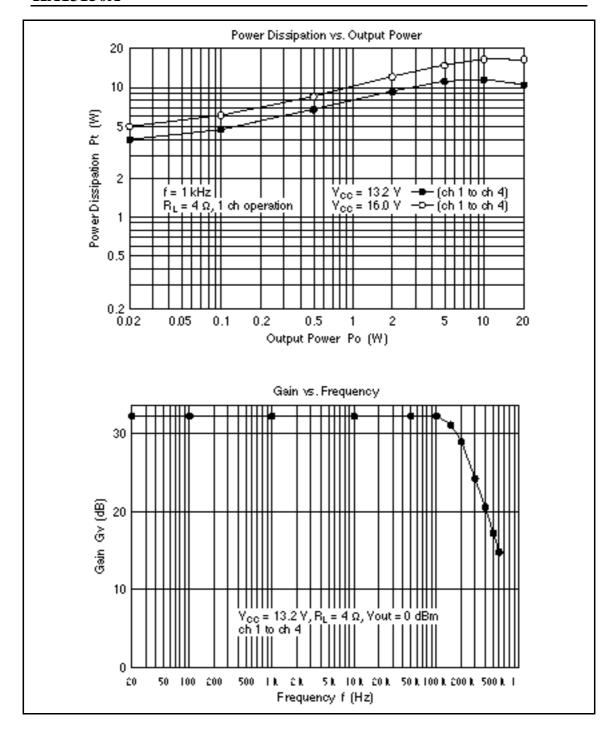












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